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MICROWAVE CORPORATION v03.0514



HMC633LC4

GaAs PHEMT MMIC DRIVER AMPLIFIER, 5.5 - 17 GHz

Typical Applications

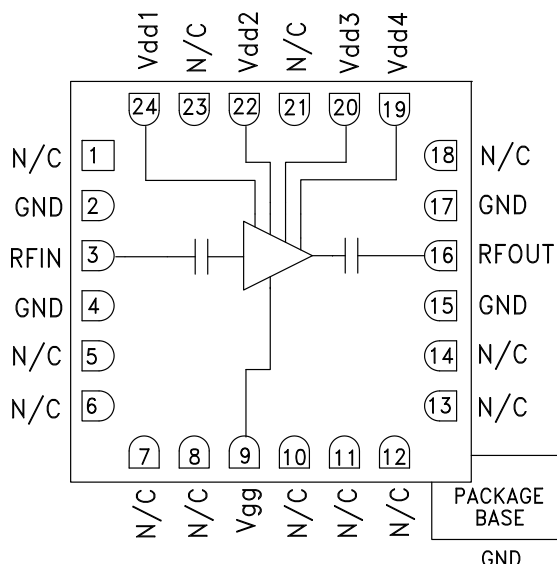
The HMC633LC4 is ideal for:

- Point-to-Point Radios
- Point-to-Multi-Point Radios & VSAT
- LO Driver for Mixers
- Military & Space

Features

Gain: 30 dB
 P1dB: +23 dBm
 Saturated Power: +23.8 dBm @ 24% PAE
 Supply Voltage: +5V @180 mA
 50 Ohm Matched Input/Output
 24 Lead Ceramic 4x4mm SMT Package: 16mm²

Functional Diagram



General Description

The HMC633LC4 is a GaAs PHEMT MMIC Driver Amplifier in a leadless 4x4 mm ceramic surface mount package which operates between 5.5 and 17 GHz. The amplifier provides up to 30 dB of gain, +30 dBm Output IP3, and +23 dBm of output power at 1 dB gain compression, while requiring 180 mA from a +5V supply. The HMC633LC4 is an ideal driver amplifier for microwave radio applications from 5.5 to 17 GHz and may be biased at +5V, 130 mA to provide 2 dB lower gain with improved PAE. The amplifier's I/Os are DC blocked and matched to 50 Ohms with no external matching required.

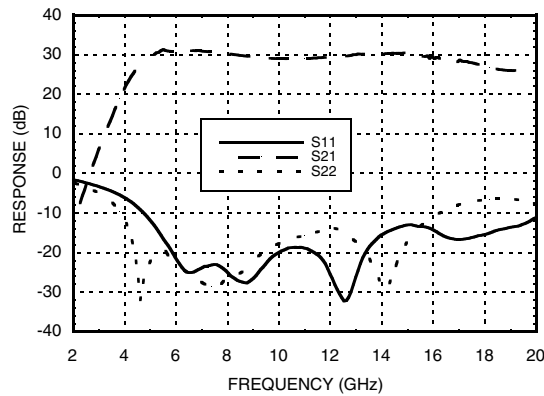
Electrical Specifications, $T_A = +25^\circ\text{C}$, $V_{dd_{1-4}} = 5\text{V}$, $I_{dd} = 180\text{mA}$ [1]

Parameter	Min.	Typ.	Max.	Min.	Typ.	Max.	Units
Frequency Range	5.5 - 9			9 - 17			GHz
Gain	26	30		25	28		dB
Gain Variation Over Temperature		0.030	0.040		0.030	0.040	dB/°C
Input Return Loss		22			17		dB
Output Return Loss		22			15		dB
Output Power for 1 dB Compression (P1dB)	20	23		18	21		dBm
Saturated Output Power (Psat)		23.8			22		dBm
Output Third Order Intercept (IP3)		30			29		dBm
Noise Figure		10			7		dB
Supply Current (Idd) (Idd = Idd ₁ + Idd ₂ + Idd ₃ + Idd ₄)		180			180		mA

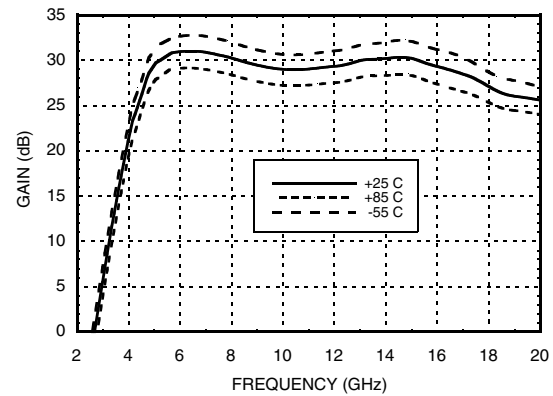
[1] Adjust Vgg between -2 to 0V to achieve Idd= 180 mA typical.

GaAs PHEMT MMIC DRIVER AMPLIFIER, 5.5 - 17 GHz

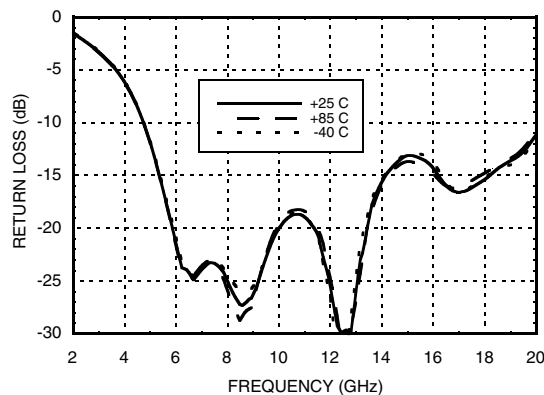
Broadband Gain & Return Loss



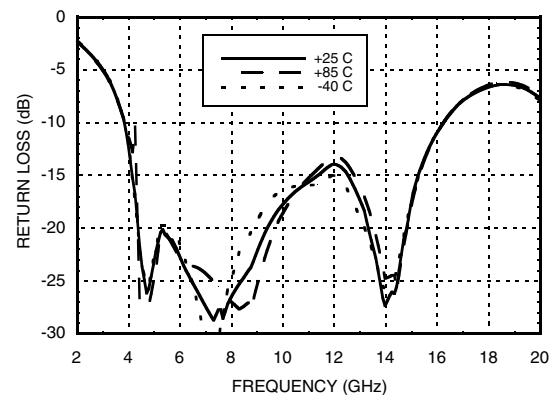
Gain vs. Temperature



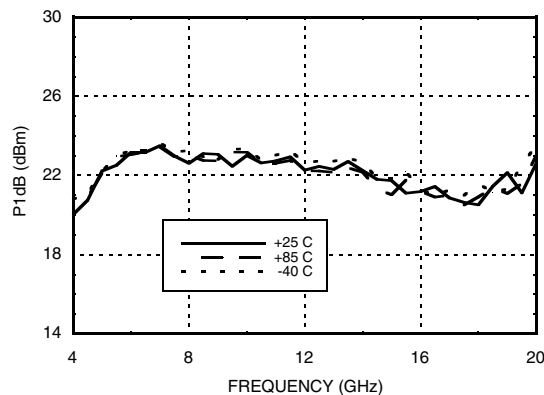
Input Return Loss vs. Temperature



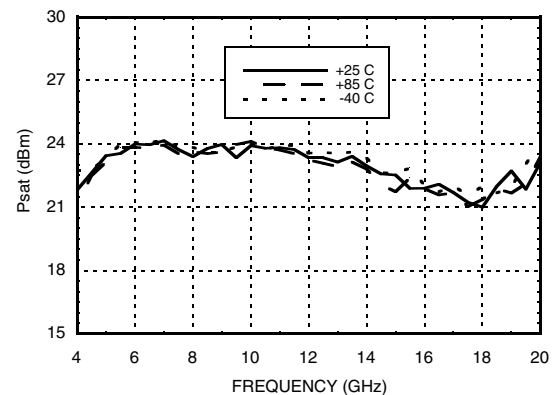
Output Return Loss vs. Temperature



P1dB vs. Temperature

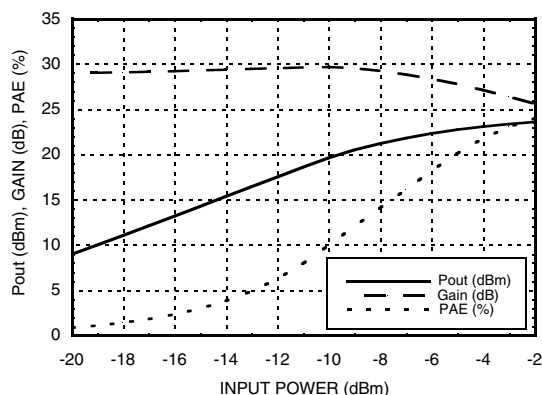
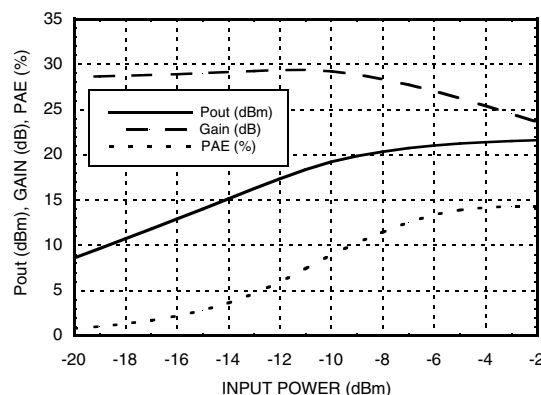
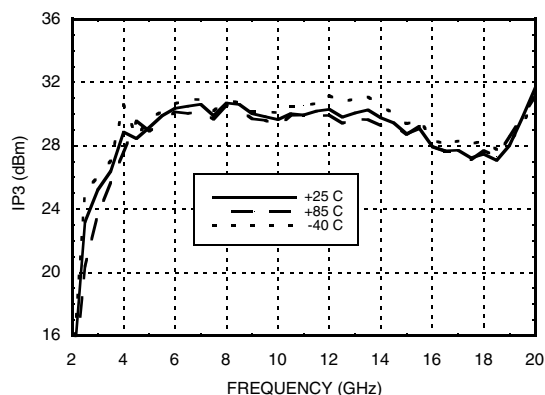
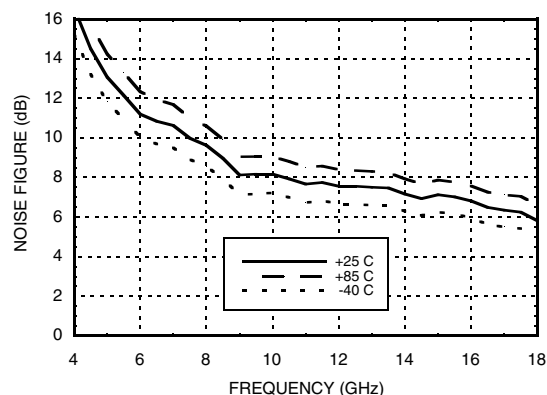
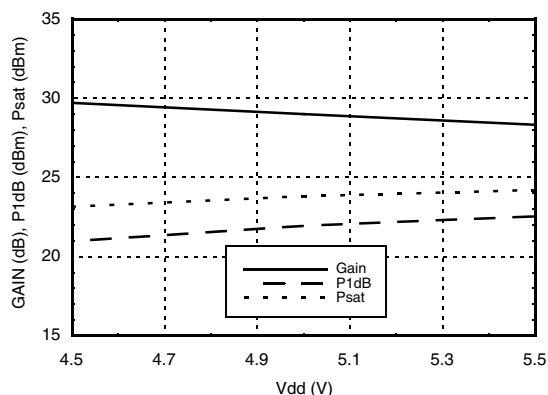
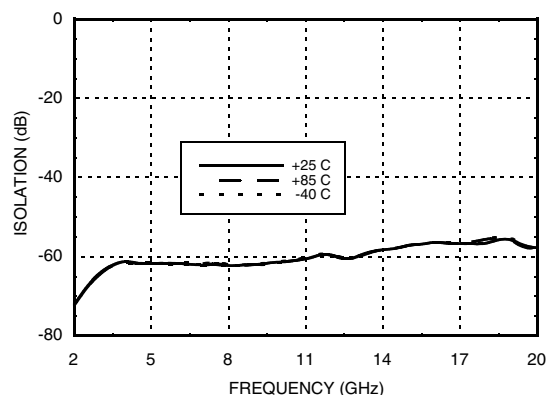


Psat vs. Temperature



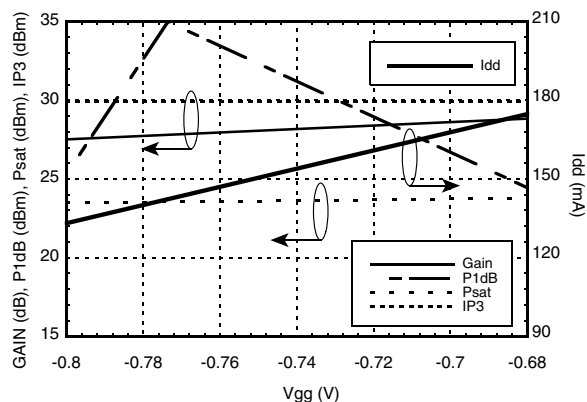


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**HMC633LC4****GaAs PHEMT MMIC DRIVER
AMPLIFIER, 5.5 - 17 GHz****Power Compression @ 11 GHz****Power Compression @ 17 GHz****Output IP3 vs. Temperature****Noise Figure vs. Temperature****Gain & Power vs. Supply Voltage @ 11 GHz****Reverse Isolation vs. Temperature**

GaAs PHEMT MMIC DRIVER AMPLIFIER, 5.5 - 17 GHz

Gain, Power & Output IP3 vs. Gate Voltage @ 11 GHz



Typical Supply Current vs. Vdd

Vdd (V)	Idd (mA)
4.5	177
5.0	180
5.5	182

Note: Amplifier will operate over full voltage ranges shown above

Absolute Maximum Ratings

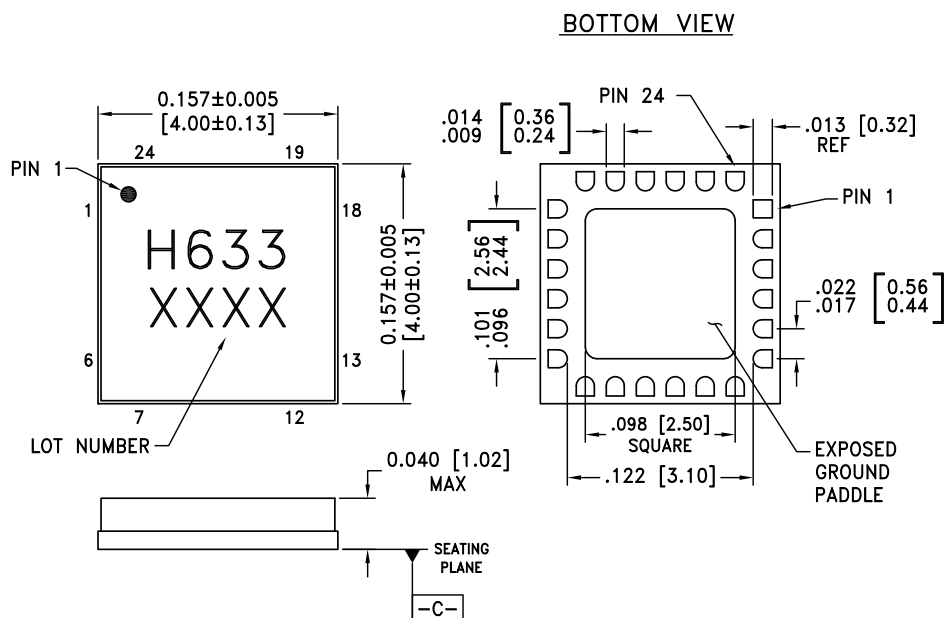
Drain Bias Voltage (Vdd1, Vdd2, Vdd3, Vdd4)	+5.5V
Gate Bias Voltage (Vgg)	-3 to 0V
RF Input Power (RFIN)(Vdd = +5 Vdc)	+5 dBm
Channel Temperature	175 °C
Continuous Pdiss (T= 85 °C) (derate 11.08 mW/°C above 85 °C)	0.99 W
Thermal Resistance (channel to package bottom)	90.23 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS



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**HMC633LC4****GaAs PHEMT MMIC DRIVER
AMPLIFIER, 5.5 - 17 GHz****Outline Drawing****NOTES:**

1. PACKAGE BODY MATERIAL: ALUMINA
2. LEAD AND GROUND PADDLE PLATING: 30-80 MICROINCHES GOLD OVER 50 MICROINCHES MINIMUM NICKEL.
3. DIMENSIONS ARE IN INCHES [MILLIMETERS].
4. LEAD SPACING TOLERANCE IS NON-CUMULATIVE.
5. PACKAGE WARP SHALL NOT EXCEED 0.05mm DATUM -C-
6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[2]
HMC633LC4	Alumina, White	Gold over Nickel	MSL3 ^[1]	H633 XXXX

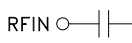
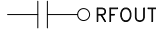
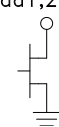
[1] Max peak reflow temperature of 260 °C

[2] 4-Digit lot number XXXX

For price, delivery and to place orders: Hittite Microwave Corporation, 2 Elizabeth Drive, Chelmsford, MA 01824

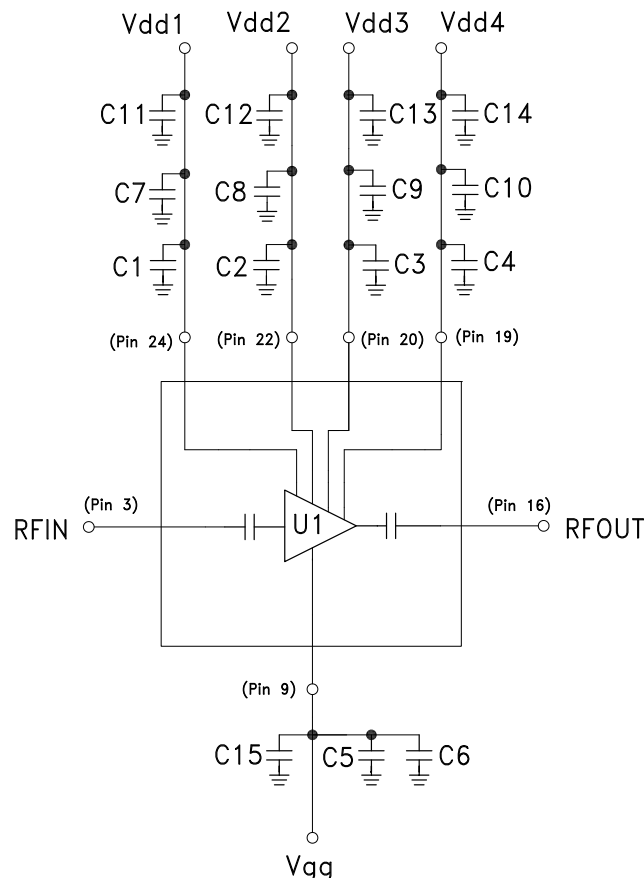
Phone: 978-250-3343 Fax: 978-250-3373 Order On-line at www.hittite.comApplication Support: Phone: 978-250-3343 or apps@hittite.com

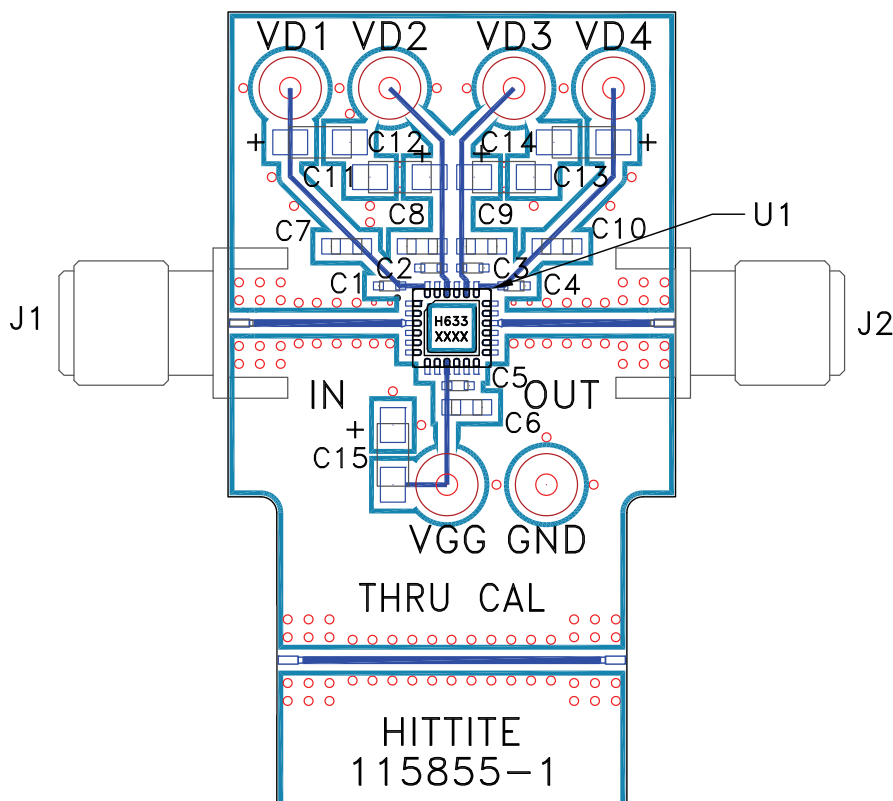
Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 5 - 8, 11 - 14, 18, 21, 23	N/C	No connection. These pins may be connected to DC/RF ground. Performance will not be affected.	
2, 4, 15, 17	GND	Package Bottom must be connected to RF/DC ground.	
3	RFIN	This pin is AC coupled and matched to 50 Ohms.	
9	Vgg	Gate control for amplifier, please follow "MMIC Amplifier Biasing Procedure" Application Note: See application circuit for required external components.	
16	RFOUT	This pin is AC coupled and matched to 50 Ohms.	
24, 22, 20, 19	Vdd1, Vdd2, Vdd3, Vdd4	Power Supply Voltage for the amplifier. See application circuit for required external components.	

Application Circuit

Component	Value
C1 - C5	100 pF
C6 - C10	1000 pF
C11 - C15	2.2 μ F



Evaluation PCB**List of Materials for Evaluation PCB 115857 ^[1]**

Item	Description
J1 - J2	2.92 mm PC Mount K-Connector
VD1 - VD4	DC Pin
C1 - C5	100 pF Capacitor, 0402 Pkg.
C6 - C10	1000 pF Capacitor, 0603 Pkg.
C11 - C15	2.2 μ F Capacitor, Tantalum
U1	HMC633LC4 Driver Amplifier
PCB [2]	115855 Evaluation PCB

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.



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HMC633LC4

**GaAs PHEMT MMIC DRIVER
AMPLIFIER, 5.5 - 17 GHz**

DRIVER & GAIN BLOCK AMPLIFIERS - SMT



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

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- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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